

Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	200.00 +/- 0.20 mm
	2.0	Notch or Flat	Notch
	3.0	Notch Direction	{110} +/- 1.0 degree
	4.0	Overall Thickness	727.10 +/- 26.00 µm
	5.0	Total Thickness Variation (TTV)	<5.00µm
	6.0	Bow	<80.00µm
	7.0	Warp	<80.00µm
	8.0	Edge Chips	0
	9.0	Edge Exclusion	7mm
HandleSilicon	10.0	Handle Growth Method	CZ
	11.0	Handle Orientation	{100} +/- 1.0 degree
	12.0	Handle Thickness	725.00 +/- 25.00 µm
	13.0	Handle Doping Type	P
	14.0	Handle Dopant	Boron
	15.0	Handle Resistivity	1~10 Ohm-cm
	16.0	Backside Finish	Lapped with oxide, lasermarking, and light handling marks
BuriedOxide	17.0	Oxide Type	Thermal
	18.0	Oxide Thickness	20,000.00 +/- 1,000.00 Å
	19.0	Oxide formed on	Handle and/or Device wafer
DeviceSilicon	20.0	Device Growth Method	CZ
	21.0	Device Orientation	{100} +/- 1.0 degree
	22.0	Mean Thickness Variation	70.00 +/- 20.00 nm
	23.0	Device Doping Type	P
	24.0	Device Dopant	Boron
	25.0	Device Resistivity	1~10 Ohm-cm
	26.0	Voids	<1cm ²
	27.0	Scratches	<10mm total length
	28.0	Haze	none

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information